

REMARKS

This is to acknowledge the rejection of all of the claims as being obvious based primarily on the disclosures of the cited Matsuda and Yamazaki patents. In response, however, each of independent Claims 1, 4, and 10 has been amended to stress the patentability of the present invention as compared to those references.

In particular, each of the independent claims now stresses that oxygen is added to a material gas comprising silicon fluoride and hydrogen, wherein the concentration of oxygen atoms is in the range 0.1 ppm to 0.5 ppm based on the concentration of silicon atoms. In this regard, it is Applicants' belief that none of the cited references suggest the concept of purposely adding oxygen to the material gas.

Looking first to the disclosure of the cited Matsuda patent, it is noted that the Examiner correctly points to Col. 34 of that patent, which, when combined with Col. 15, implies the use of a gas including silicon fluoride, hydrogen, and oxygen. However, nothing in that patent suggests the addition of oxygen to the remainder of the gasified compound. Instead, at Col. 15, lines 34-35, Matsuda suggests that a compound including oxygen must be gasified, not gasification followed by the addition of oxygen.

The Examiner also correctly noted that Matsuda does not disclose the claimed concentration of oxygen atoms, wherefore the two Yamazaki patents are cited. Applicants respectfully submit, however, that no matter how one may attempt to combine the cited references, there is no suggestion of adding oxygen to the material gas including silicon fluoride and hydrogen. Again, although oxygen may exist in the compound which is to be gasified, there

is no suggestion to add oxygen to the previously gasified product of silicon fluoride and hydrogen.

In conclusion, Applicants point to the paragraph commencing at page 25, line 25, of the Specification as providing support for the concept now stressed in the claims. Also, it is emphasized that the claimed invention provides a high quality silicon thin film formed at high speed and having excellent crystallinity.

For all of these various reasons Applicants respectfully submit that the amended claims are all allowable, and a formal Notice of Allowance is solicited.

Applicants' undersigned attorney may be reached in our New York Office by telephone at (212) 218-2100. All correspondence should continue to be directed to our address listed below.

Respectfully submitted,



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